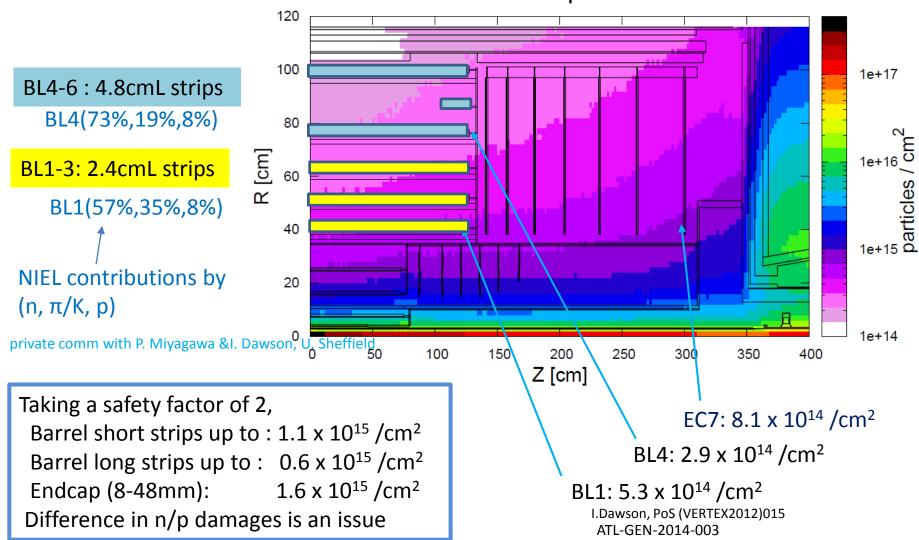
Charge Collection and Field Profile Studies in Heavily Irradiated Silicon Strip Sensors for the ATLAS Inner Tracker Upgrade

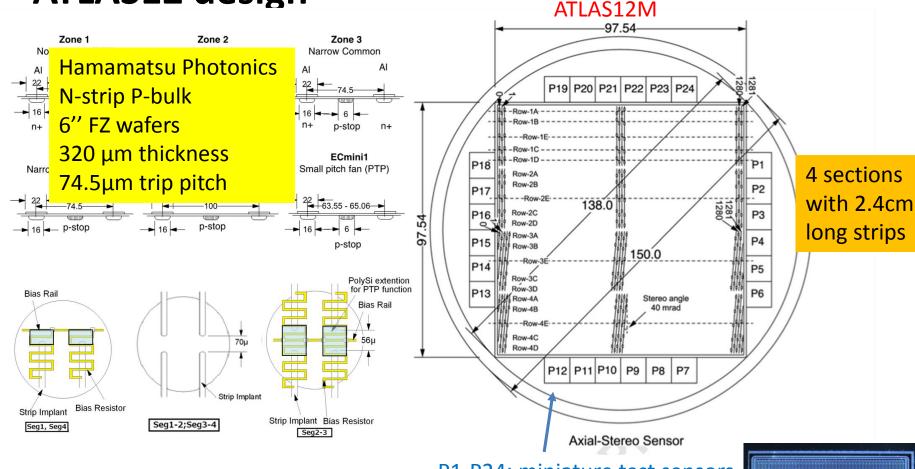


## ATLAS ITk Lol Layout and Fluence at HL-LHC

Fluence evaluations per 3000 fb<sup>-1</sup> 1 MeV neutron equivalent fluence



## ATLAS12 design



#### Hamamatsu FZP320 wafers (3-8 k $\Omega$ cm)

ATLAS12A ---  $\rho$ ~3.5-5 k $\Omega$ cm ATLAS12M ---  $\rho$ ~6 k $\Omega$ cm

ATLAS07  $\rho$ ~5-5.5 k $\Omega$ cm

P1-P24: miniature test sensors 1x1cm, strips 8 mm long

used for rad-hard study

#### **Irradiation**

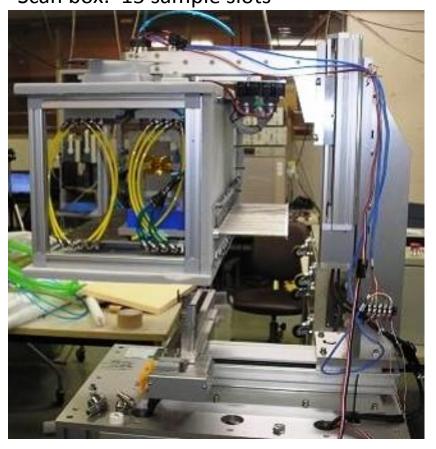
Neutron irradiation: Ljubljana reactor

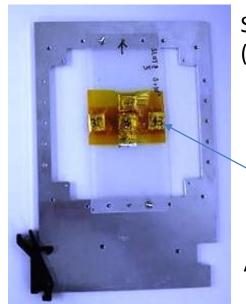
Pion irradiation:

Proton irradiations: Karlsruhe 23 MeV

Sirmingham 27 MeV All damages translated fluence Birmingham 27 MeV to 1-MeV to 1-MeV

Irradiation example: CYRIC (Tohoku Univ) Scan box: 15 sample slots



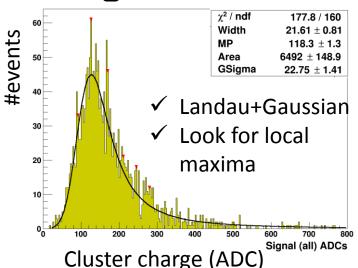


Sample holder/slot (11x11cm opening)

Al<sup>27</sup>(p, 3pn)**Na<sup>24</sup>** Al foils for dosimetry

CYRIC case:

For  $10^{12} \sim 10^{16}$ /cm<sup>2</sup> range irradiation, A few min  $^{\sim}6$  hrs at beam current  $10nA^{\sim}1\mu A$  **Charge Collection Measurement Consistency** 



β-source (electron beam)

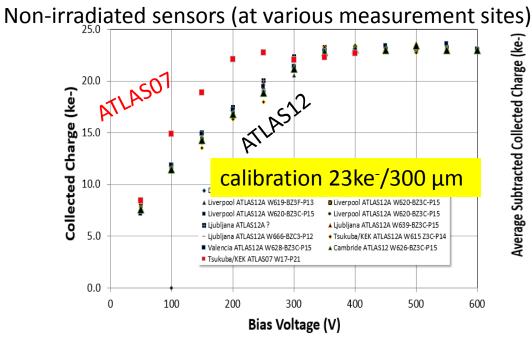
Alivaba:

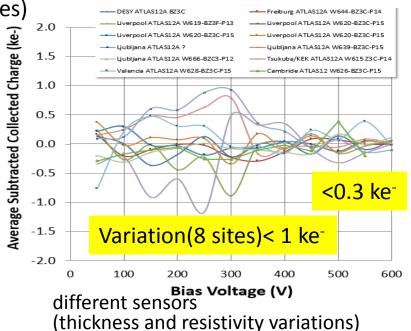
FPGA based DAQ system

LHCb Beetle chip



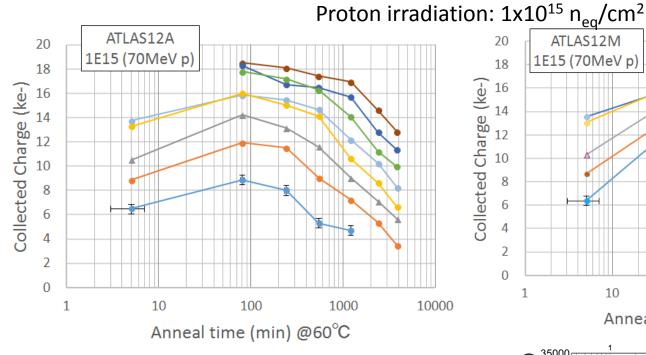
http://www.alibavasystems.com/

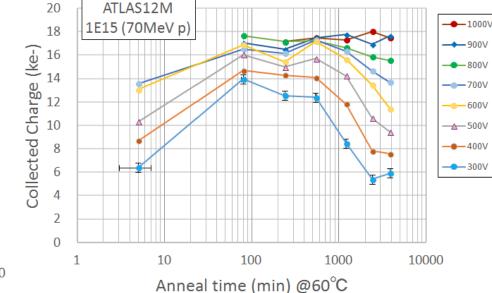




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## Long term annealing at 60°

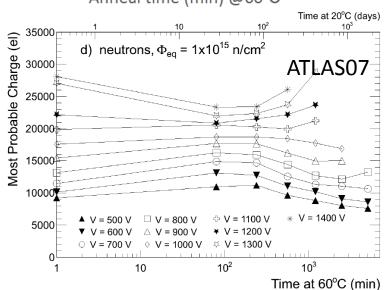




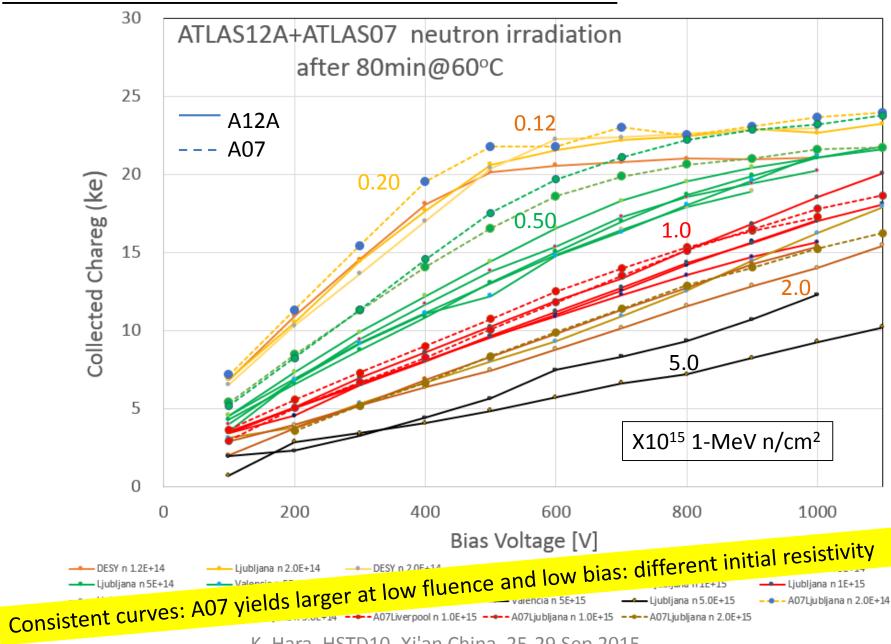
- Annealing is similar for A12A/A12M for bias below 600V (proton 1E15/cm²)
- A07 (neutron) studied previously
   => behavior similar to A12M

   I. Mandic et al., NIMA 629 (2011) 101

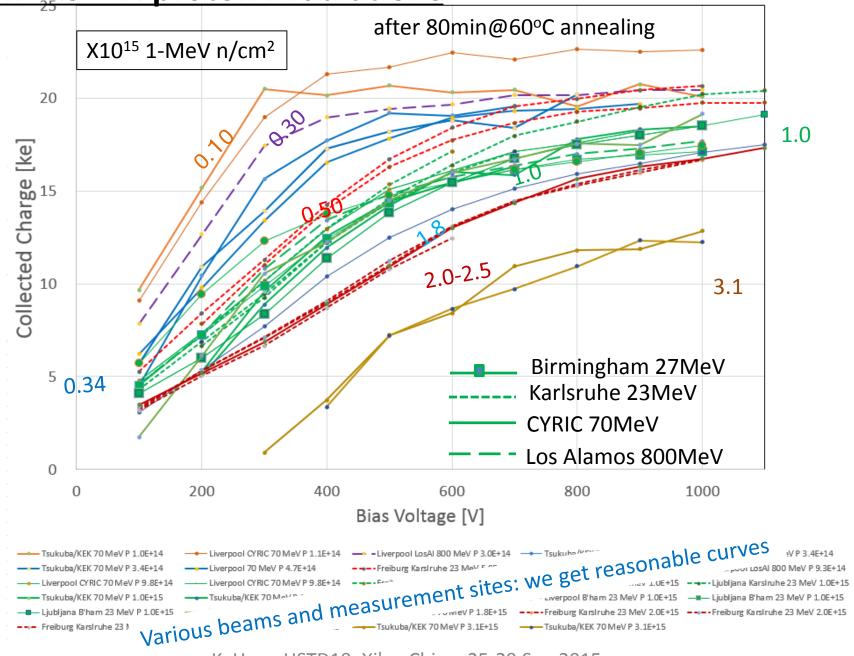
All data shown below are after controlled annealing of 80min @ 60°C

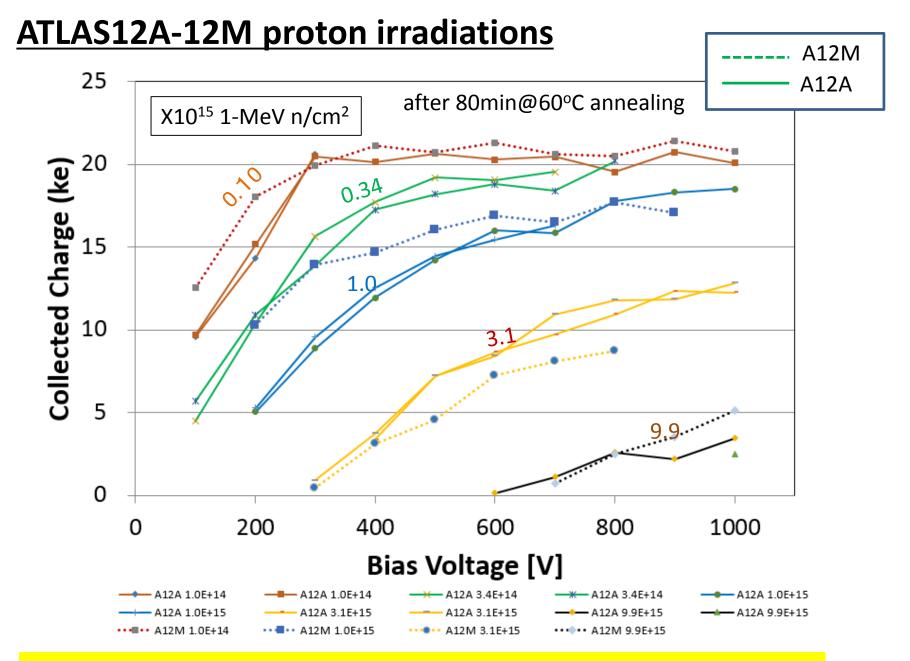


## ATLAS12A+ATLAS07 Neutron irradiation



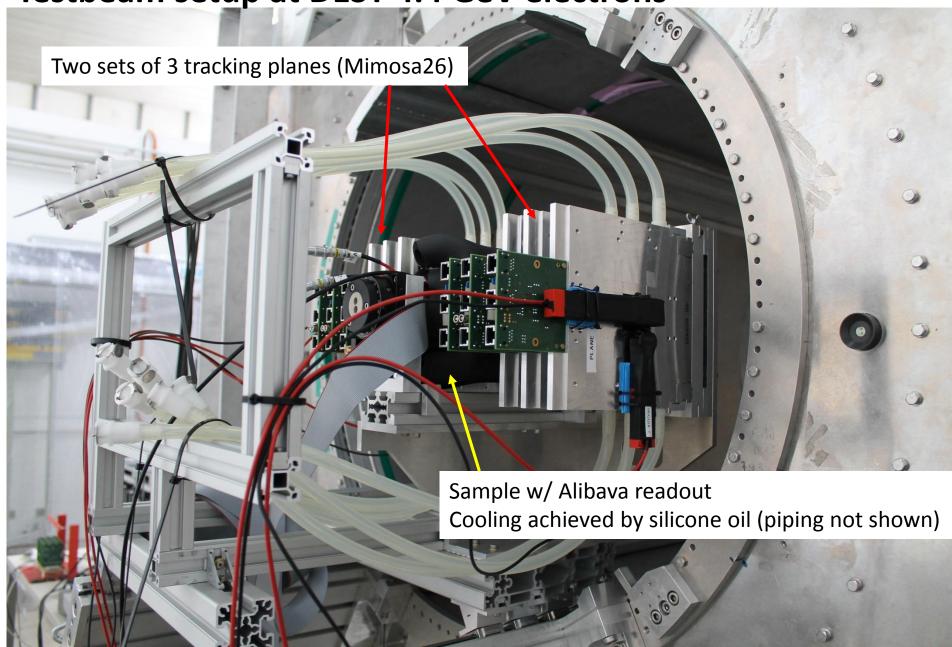
**ATLAS12A proton irradiations** X10<sup>15</sup> 1-MeV n/cm<sup>2</sup>



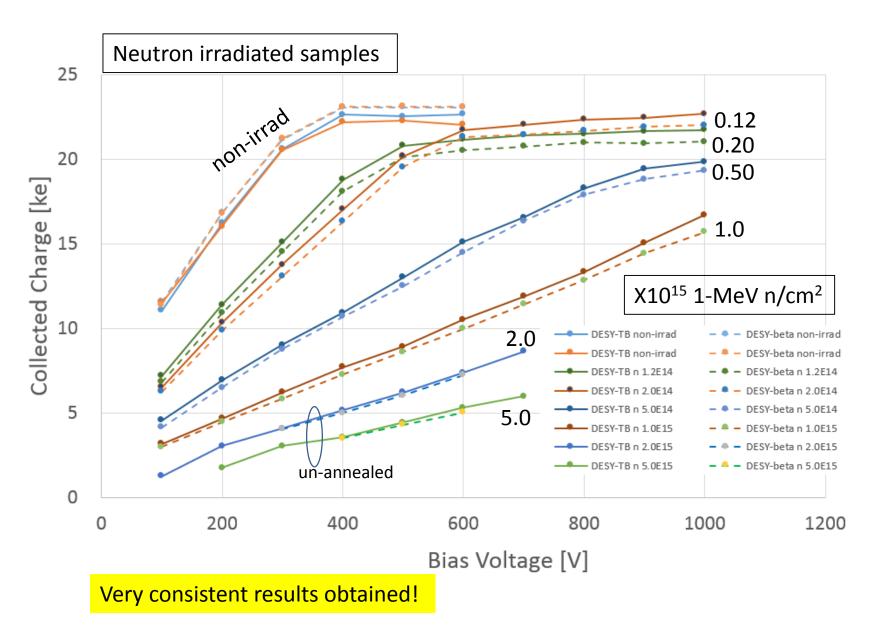


12M yields larger signal at low fluence and at low bias: different initial resistivity

**Testbeam setup at DESY 4.4 GeV electrons** 

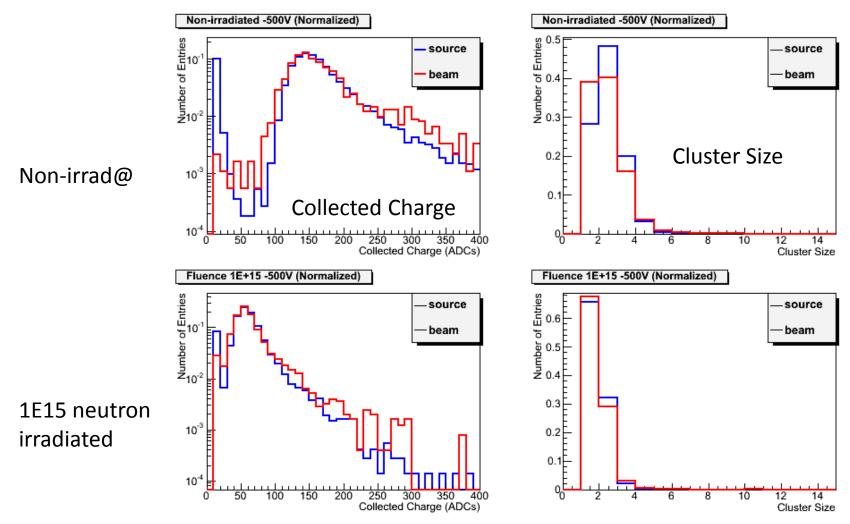


## Source vs testbeam (DESY 4.4-GeV electrons)



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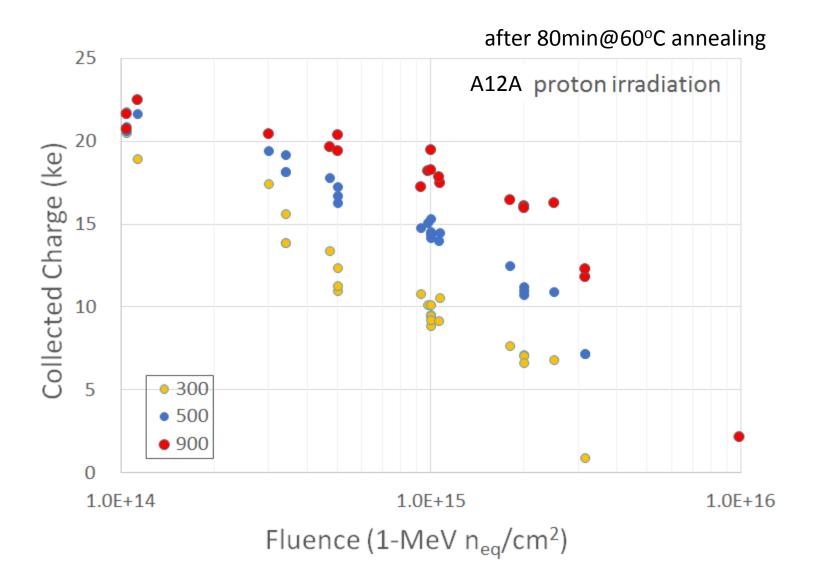
## Source vs testbeam (DESY 4.4-GeV electrons)



Source vs beam:

Charge distributions in reasonable agreement Cluster Size slightly wider for source as expected

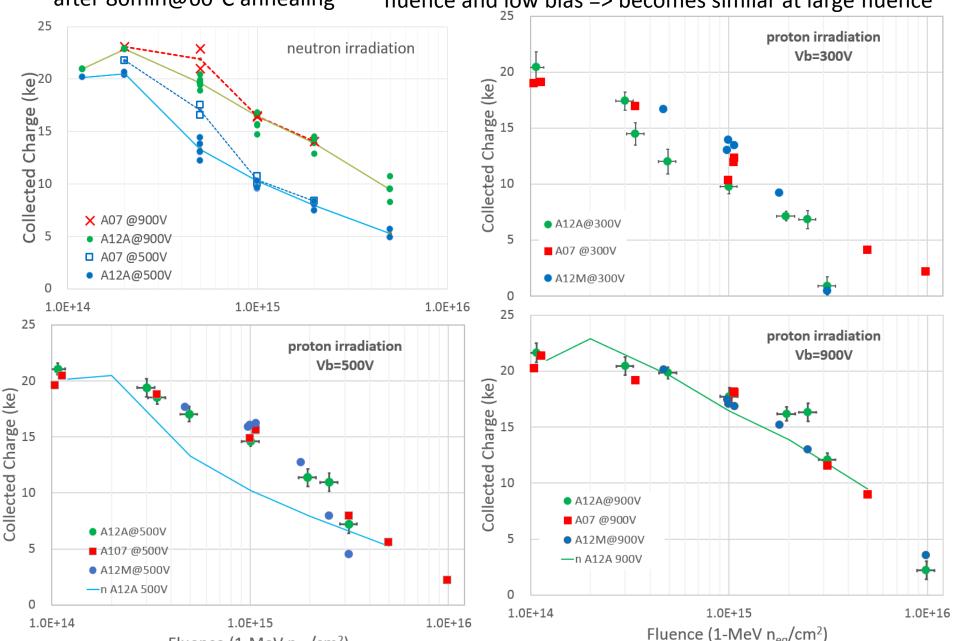
## Fluence dependence (all A12A data points)



## Fluence dependence

after 80min@60°C annealing

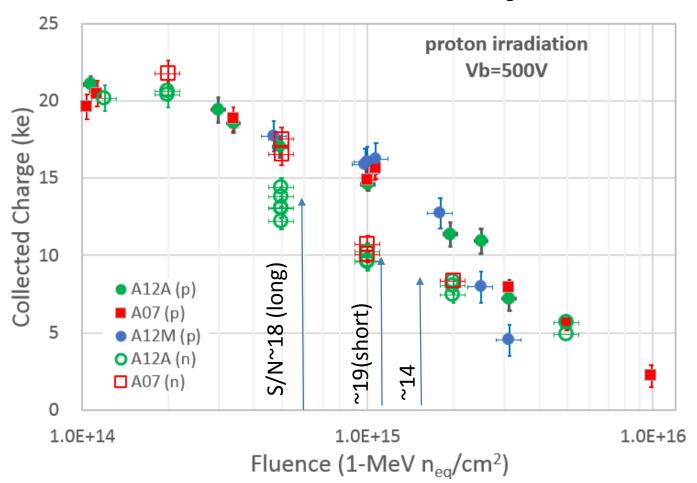
A12A yield slightly smaller & n-damage is larger at low fluence and low bias => becomes similar at large fluence



## S/N at HL-LHC

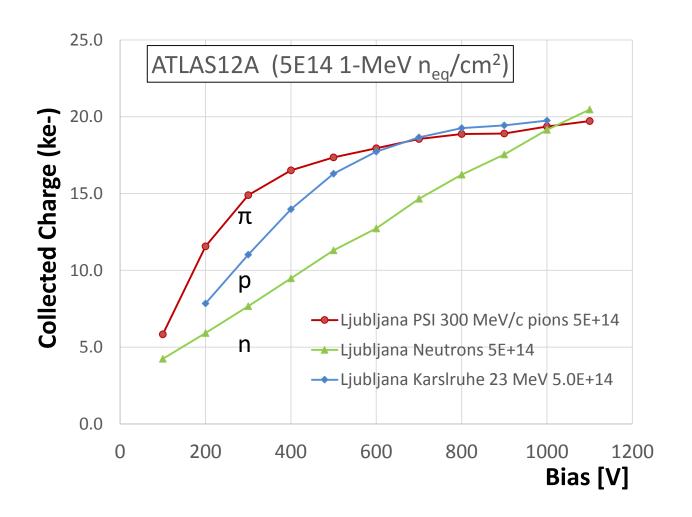
Barrel short (24mm)strips up to :  $1.1 \times 10^{15}$  /cm<sup>2</sup> Barrel long (48mm) strips up to :  $0.6 \times 10^{15}$  /cm<sup>2</sup> Endcap (8-48mm) strips: max  $1.6 \times 10^{15}$  /cm<sup>2</sup>

#### ENC noise ~550/720/650 ENC for barrel short/barrel long/EC innermost strips



At Vb=500V, strip detectors remain as precision tracker after HL-LHC fluence

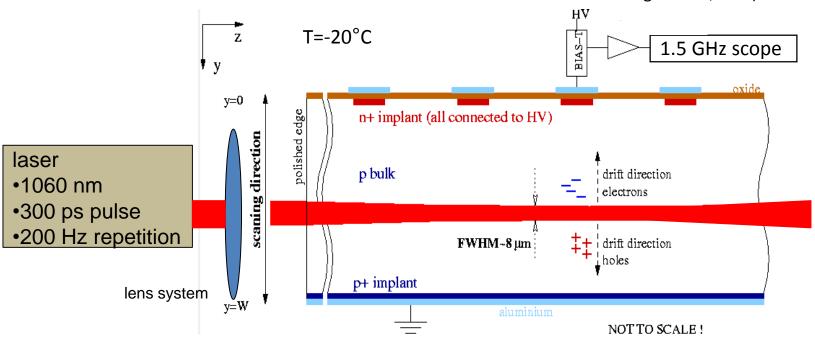
## Charge collection of samples irradiated with $p/n/\pi$



Different CCE curves measured for the same NIEL fluence Investigated E-field profile using e-TCT technique

edge TCT (transient current technique)

G. Kramberger et al., PoS (VERTEX2012) 022



IR laser injected from polished side scanning depthwise to investigate the charge collection dependence in depth => E-field distribution in depth

Polished edge

detectors on a Peltier cooled support in dry air atmosphere (down to -20°C)

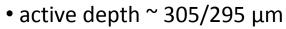
K. Hara, HSTD10, Xi'an China, 25-29 Sep 2015



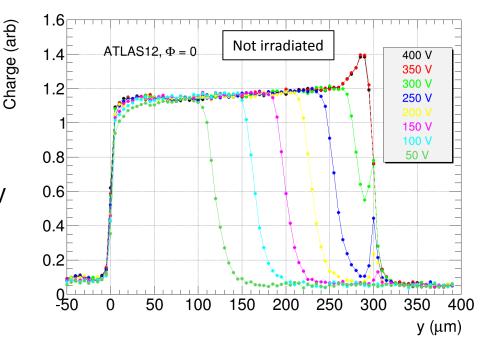
# **e-TCT** non-irradiated samples

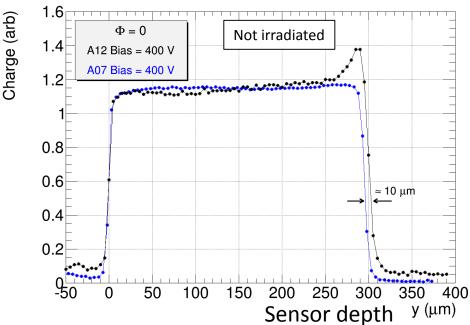
Charge vs. depth

 A12A detector depleted at 350 V (A07 deplete at 200V)



A12A about 10 µm more than
 A07 → as expected from physical thicknesses
 (320/310 µm for A12A/A07)



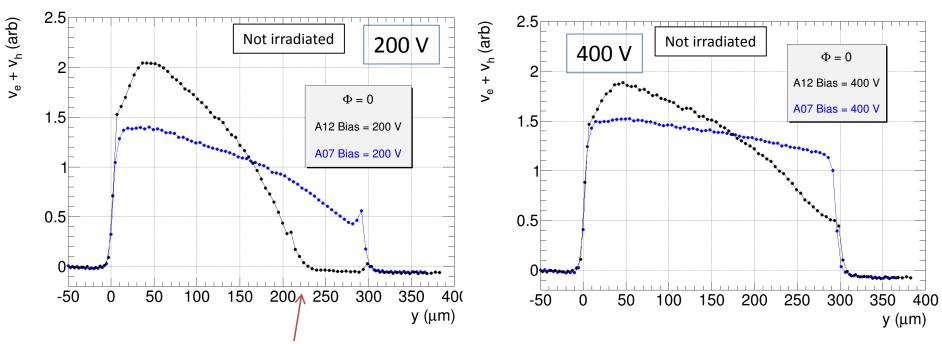


#### **Velocity profile**

$$I(y, t \sim 0) \approx qE_w(y) \left[ \overline{v}_e(y) + \overline{v}_h(y) \right] \propto E; \quad \overline{v}_e(y) + \overline{v}_h(y) \propto E$$

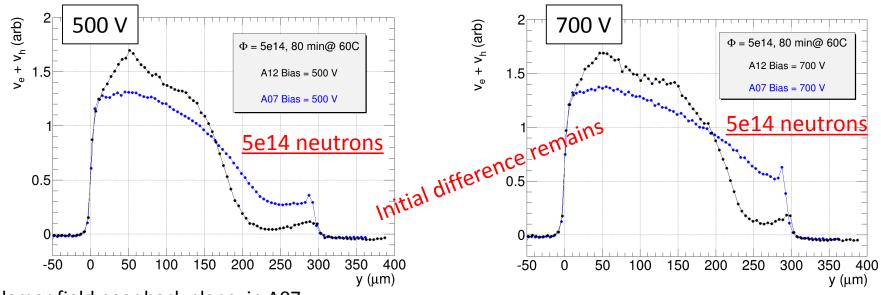
- induced current at  $t \sim 0$  proportional to carrier velocity and weighting field at laser spot location ( $E_w \sim \text{constant}$ , see: G. Kramberger, et al.,IEEE TNS NS-57 (2010) 2294.)
- if E not too large, I proportional to e-filed E
- plots normalized to same integral from 0-300 μm (because ∫ Edx = Bias)
  - at 200 V A07 depleted, A12A not depleted

• at 400 V both depleted

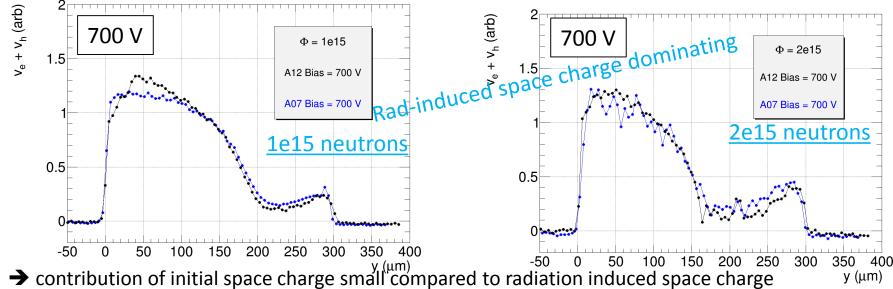


 $\rightarrow$  expected depletion depth for A12A at 200 V 220  $\mu$ m!

#### **Edge-TCT with detectors irradiated in Ljubljana (neutron)**

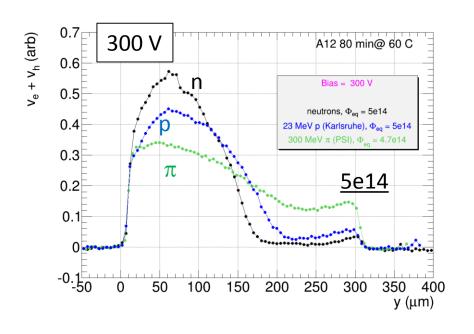


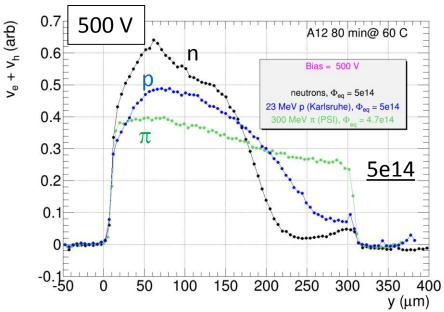
- larger field near back plane in A07
- → roughly in agreement with expectation because of different initial resistivities



K. Hara, HSTD10, Xi'an China, 25-29 Sep 2015

#### **Edge-TCT with detectors irradiated by protons/neutrons/pions**

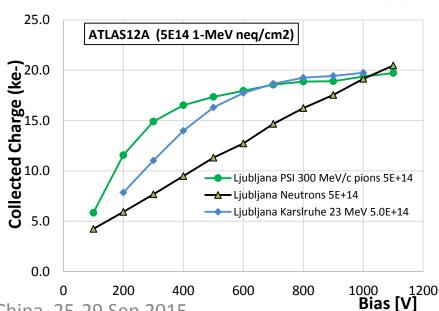




#### consistent with CCE measurements

- → more CC after charged particle irradiation
- → more CC for pions than for 23 MeV protons:
  - → larger E field at back side after pion irrad than after 23 MeV proton irradiation.

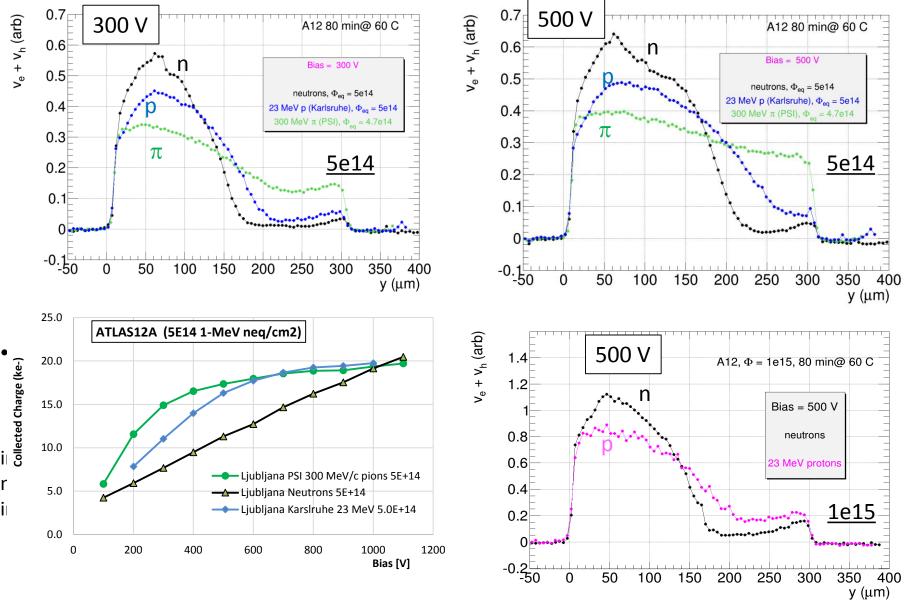
At moderate bias, CC is least after neutron irradiation



### **Summary**

- 1. CC of HPK p-bulk sensors irradiated with protons and neutrons are evaluated extensively with  $\beta$ -ray by several institutions in collaboration
  - $\square$  CC of >9 Ke<sup>-</sup> can be maintained at Vb=500V after 1.6x10<sup>15</sup> 1-MeV n<sub>eq</sub>/cm<sup>2</sup>
    - S/N> 19 for short strips (L=2.4cm) after  $1.1 \times 10^{15}$  1-MeV  $n_{eq}/cm^2$
    - S/N> 18 for long strips (L=4.8cm) after  $0.6x10^{15}$  1-MeV  $n_{eq}/cm^2$
    - S/N> 14 for innermost EC after 1.6x10 $^{15}$  1-MeV  $n_{eq}/cm^2$
- 2.  $\beta$ -ray measurements are validated by beam
- 3. Difference in p/n/pion damages investigated in terms of electric-field profiles using e-TCT
  - Reduction in the charge collection due to induced traps
  - Change in the field profile across depth due to generated currents Both dependent on the irradiation particles  $(n/p/\pi)$ 
    - ✓ Defect introduction rates are more in the order of :  $n>p>\pi$
    - ✓ Differences in E-filed profile shapes due to double peak E-field:
    - ⇒ HPK p-bulk strip sensors are operational at the HL-LHC fluence

#### **Edge-TCT with detectors irradiated by protons/neutrons/pions**



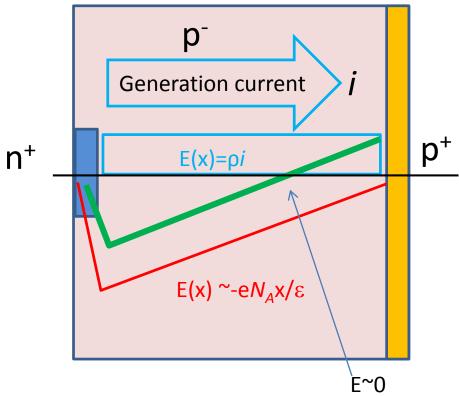
#### Double Peak E-field V. Eremin et al. NIMA535 (2004)622.

$$\rho_{eff} = \rho_{dopants} \sim -eN_A$$
 ... space-charge density

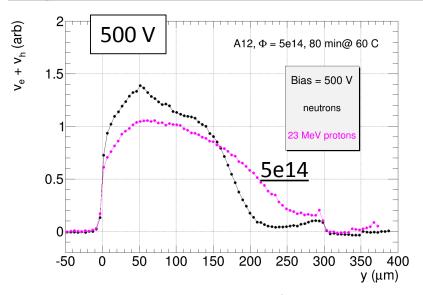


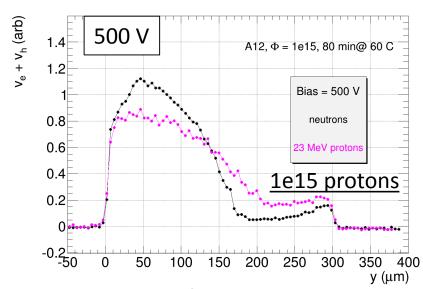
$$\rho_{eff} = e(f_D n_D - f_A n_A) + \rho_{dopants}$$

radiation induced trapping levels with occupancies f



#### Edge-TCT with detectors irradiated in Karlsruhe (p 23 MeV)





larger active volume after irradiation with 23 MeV protons than after neutrons at 500 V
 → consistent with larger charge measured with Alibava

